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Vishay Siliconix

Powered-off Protection, 0.85 Ω , 1.8 V to 5.5 V, SPDT Analog Switch (2:1 Multiplexer)

DESCRIPTION

The DG2001E is a high performance single-pole, double-throw (SPDT) analog switch designed for 1.8 V to 5.5 V operation with a single power rail.

Fabricated with high density CMOS technology, the device achieves low on resistance of $0.85~\Omega$ at a 5 V power supply, low power consumption, and fast switching speeds.

The DG2001E can handle both analog and digital signals and permits signals with amplitudes of up to V+ to be transmitted in either direction. Its control logic inputs can go over V+ up to 5.5 V. The control logic input high threshold is guaranteed as low as 1.8 V over the power supply range up to 5.5 V. It features break before make switching performance.

A powered-off protection circuit is built into the switch to prevent an abnormal current flow from COM pin to V+ during the power-down condition. Each output pin can withstand greater than 7 kV (human body model).

Operation temperature is specified from -40 °C to +85 °C. The DG2001E is available in TSOP-6 package.

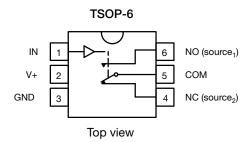
FEATURES

- Low switch on-resistance (0.85 Ω)
- 1.8 V to 5.5 V single supply operation
- Isolation in powered-off mode
- Guaranteed 1.8 V logic high
- Control logic inputs can go over V+
- Low charge injection (8 pC)
- · Break before make switching
- Latch-up performance exceeds 300 mA per JESD 78
- ESD tested
 - 7000 V human body model (JS-001)
 - 1000 V charge device model (JS-002)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Consumer and computing
- · Portable instrumentation
- Medical equipment
- Battery operated systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device marking: H1

	H1XXX	
Pin 1 —	•	

Device marking: H1XXX XXX = date / lot traceability code

TRUTH TABLE					
LOGIC	NC	NO			
0	On	Off			
1	Off	On			

ORDERING INFORMATION						
TEMP RANGE	PACKAGE	PART NUMBER				
-40 °C to +85 °C	TSOP-6	DG2001EDV-T1-GE3				

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ABSOLUTE MAXIMUM RATIN	GS (T _A = 25 °C, unless otherwise noted)		
PARAMETER	LIMIT	UNIT	
V+, COM, NC, NO, IN reference to GND		-0.3 to 6	V
Continuous current (any terminal)		± 50	mΛ
Peak current (pulsed at 1 ms, 10 % duty of	cycle)	± 200	mA
Storage temperature (D suffix)		-65 to +125	°C
Power dissipation (packages) ^a	TSOP-6 b	570	mW
ESD / HBM	JS-001	7000	V
ESD / CDM	JS-002	1000	V
Latch up	Per JESD78 with 1.5 x voltage clamp	300	mA

Notes

- a. All leads welded or soldered to PC board
- b. Derate 7 mW/°C above 25 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+ = 5 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED		LIMITS -40 °C to +85 °C			UNIT
		$V+ = 5 V, \pm 10 \%$ $V_{IN} = 0.8 V \text{ or } 2.4 V^{e}$		MIN. b	TYP. °	MAX. b	
Analog Switch							
Analog signal range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
On-resistance	R _{ON}	$V_{+} = 4.5 V$ $V_{COM} = 3 V, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full	-	0.85	1.6 1.8	
R _{ON} flatness ^d	R _{ON} Flatness	$V_{\text{COM}} = 0 \text{ V}, \text{ NNO, NNC} = 10 \text{ m/s}$ $V_{\text{COM}} = 0 \text{ V to V+, I_{NO, I_{NC}}} = 10 \text{ mA}$	Room	-	0.3	-	Ω
	I _{NO(off)}		Room	-5	-	5	
Switch off	I _{NC(off)}	V+ = 5.5 V	Full	-30	-	30	
leakage current ^g	loovy m	V_{NO} , $V_{NC} = 1 \text{ V} / 4.5 \text{ V}$, $V_{COM} = 4.5 \text{ V} / 1 \text{ V}$	Room	-5	-	5	nA
	I _{COM(off)}		Full	-30	-	30	117 (
Channel-on	1	V+ = 5.5 V	Room	-5	-	5	
leakage current ^g	I _{COM(on)}	V_{NO} , $V_{NC} = V_{COM} = 1 \text{ V} / 4.5 \text{ V}$	Full	-30	-	30	
Power down leakage	I _{COM(PD)}	V+ = 0 V, V _{COM} = 4.5 V, V _{IN} = GND	Full ^d	-	-	1	μA
Digital Control							
Input high voltage	V _{INH}		Full	2.4	-	-	V
Input low voltage	V _{INL}		Full	-	-	0.8	V
Input capacitance	C _{IN}		Full	-	3	-	рF
Input current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	-1	-	1	μA
Dynamic Characteristics							
T Par			Room	-	15	32	
Turn-on time	t _{ON}		Full	-	-	35	
T ""	1 .	V_{NO} or V_{NC} = 3 V, R_L = 300 Ω , C_L = 35 pF	Room	-	6	26	ns
Turn-off time	t _{OFF}		Full	-	-	31	
Break-before-make time	t _d		Room	1	4	-	
Charge injection d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	8	-	рС
Off-isolation d	OIRR		Room	-	-63	-	-
Crosstalk d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	-	-63	-	dB
Source-off capacitance d	$C_{NO(off)} \ C_{NC(off)}$	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	16	-	pF
Channel-on capacitance d	C _{ON}		Room	-	53	-	
Power Supply							
Power supply current	I+	$V_{IN} = 0 \text{ V or V} +$	Full	_	0.0003	1	μA



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PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. a	LIMITS -40 °C to +85 °C			UNIT
	01111202	$V+ = 3 V, \pm 10 \%$ $V_{IN} = 0.4 V \text{ or } 2 V^e$		MIN. b	TYP. c	MAX. b	ONIT
Analog Switch							
Analog signal range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0	-	V+	V
On-resistance	R _{ON}	V+ = 2.7 V	Room	-	1.6	2.2	
	OIV	$v_{COM} = 1.5 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$		-	-	2.6	Ω
R _{ON} flatness ^d	R _{ON} Flatness	V+ = 2.7 V $V_{COM} = 0 V \text{ to V+, } I_{NO}, I_{NC} = 10 \text{ mA}$	Room	-	0.6	1	
	I _{NO(off)}		Room	-5	-	5	
Switch off	I _{NC(off)}	V+ = 3.3 V	Full	-15	-	15	
leakage current ^g		V_{NO} , $V_{NC} = 1 \text{ V} / 3 \text{ V}$, $V_{COM} = 3 \text{ V} / 1 \text{ V}$	Room	-5	-	5	
	I _{COM(off)}		Full	-15	-	15	nA
Channel-on		V+ = 3.3 V	Room	-5	-	5	
leakage current ^g	I _{COM(on)}	$V_{NO}, V_{NC} = V_{COM} = 1 \text{ V} / 3 \text{ V}$	Full	-15	-	15	
Digital Control				I.			<u> </u>
Input high voltage	V _{INH}		Full	2	-	-	V
Input low voltage	V _{INL}		Full	-	-	0.4	V
Input capacitance	C _{IN}		Full	-	-	-	pF
Input current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time	+		Room	-	21	42	
rum-on time	t _{ON}		Full	-	-	47	
Turn-off time		V_{NO} or V_{NC} = 2 V, R_L = 300 Ω , C_L = 35 pF	Room	-	9	32	ns
rum-on time	t _{OFF}		Full	-	-	35	
Break-before-make time	t _d		Room	1	7	-	
Charge injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	6	-	рС
Off-isolation d	OIRR	D = 50 0 C = 5 ~ C 4 MHz	Room	-	-63	-	40
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	-	-63	-	dB
N _O , N _C off capacitance ^d	$C_{NO(off)} \ C_{NC(off)}$	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	16	-	рF
Channel-on capacitance d	C _{ON}	·	Room	-	54	-]
Power Supply							
Power supply current	I+	V _{IN} = 0 V or V+	Full	-	0.00002	1	μA
							•



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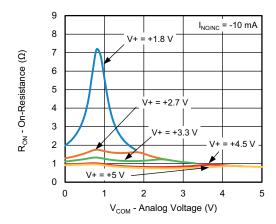
SPECIFICATIONS (V+	= 2 V)						
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.a	LIMITS -40 °C to +85 °C			UNIT
TADAMETER	OTMBOL	$V+ = 2 V, \pm 10 \%$ $V_{IN} = 0.4 V \text{ or } 1.6 V^{e}$	I LIVII .	MIN. b	TYP. c	MAX. b	Oitii
Analog Switch							
Analog signal range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
On-resistance	R _{ON}	V+ = 1.8 V	Room	-	6	8	
OII-Tesistarice	TION	$V_{COM} = 1 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Full	ı	-	10	Ω
R _{ON} flatness ^d	R _{ON} Flatness	V+ = 1.8 V $V_{COM} = 0 V to V+, I_{NO}, I_{NC} = 10 mA$	Room	ı	6	-	
	I _{NO(off)}		Room	-0.5	-	0.5	
Switch off	I _{NC(off)}	V+ = 2.2 V	Full	-5	-	5	
leakage current ^g		V_{NO} , $V_{NC} = 0.5 \text{ V} / 1.5 \text{ V}$, $V_{COM} = 1.5 \text{ V} / 0.5 \text{ V}$	Room	-0.5	-	0.5	^
	I _{COM(off)}	OOW	Full	-5	-	5	nA
Channel-on		V+ = 2.2 V	Room	-0.5	-	0.5	
leakage current ^g	I _{COM(on)}	V_{NO} , $V_{NC} = V_{COM} = 0.5 \text{ V} / 1.5 \text{ V}$	Full	-5	-	5	
Digital Control							
Input high voltage	V _{INH}		Full	1.6	-	-	V
Input low voltage	V _{INL}		Full	-	-	0.4	V
Input capacitance	C _{IN}		Full	-	3	-	pF
Input current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time	+		Room	-	36	51	
rum-on time	t _{ON}		Full	1	-	62	
Turn-off time	+	V_{NO} or V_{NC} = 1.5 V, R_L = 300 Ω,C_L = 35 pF	Room	1	16	40	ns
rum-on time	t _{OFF}		Full	-	-	43	
Break-before-make time	t _d		Room	1	16	-	
Charge injection ^d	Q_{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room	1	21	-	рС
Off-isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 1 MHz$	Room	1	-63	-	dB
Crosstalk ^d	X _{TALK}	$n_L = 30.52$, $O_L = 3 \text{ pr}$, $I = 1 \text{ IVIDZ}$	Room	-	-63	-	ub
N _O , N _C off capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	ı	16	-	pF
Channel-on capacitance d	C _{ON}		Room	1	52	-	
Power Supply							
Power supply current	l+	V _{IN} = 0 V or V+	Full	-	0.00001	1	μΑ

Notes

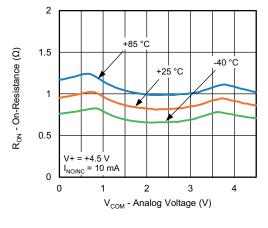
- a. Room = 25 °C, full = as determined by the operating suffix
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- c. Typical values are for design aid only, not guaranteed nor subject to production testing
- d. Guarantee by design, nor subjected to production test
- e. V_{IN} = input voltage to perform proper function
- f. Guaranteed by 5 V leakage testing, not production tested



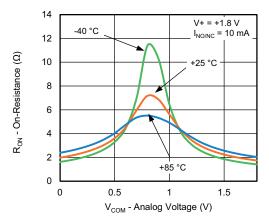
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



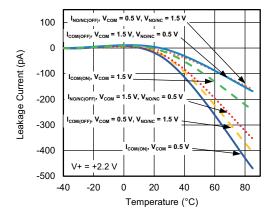
 $R_{DS(on)}$ vs. V_{COM} and Supply Voltage



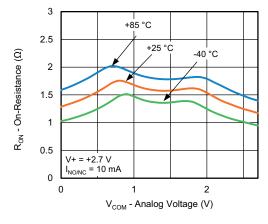
 $R_{\text{DS(on)}}\, \text{vs.}\, V_{\text{COM}}$ and Temperature



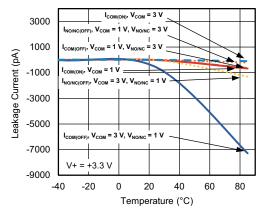
R_{DS(on)} vs. V_{COM} and Temperature



Leakage Current vs. Temperature



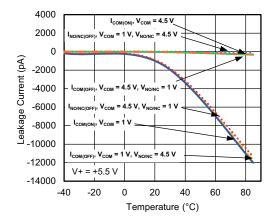
 $R_{\text{DS(on)}}\,\text{vs.}\,V_{\text{COM}}$ and Temperature



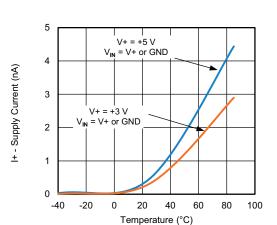
Leakage Current vs. Temperature



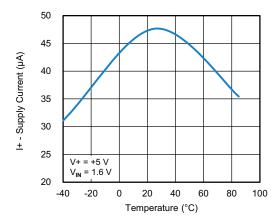
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



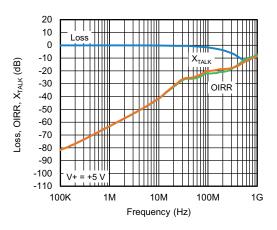
Leakage Current vs. Temperature



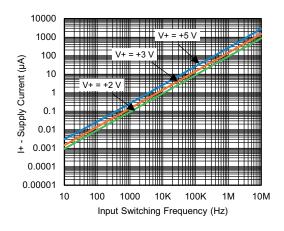
Supply Current vs. Temperature



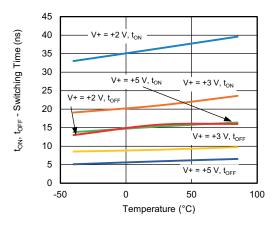
Supply Current vs. Temperature



Insertion Loss, Off-Isolation Crosstalk vs. Frequency



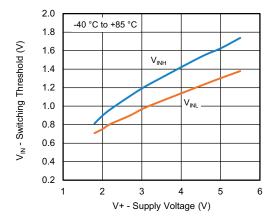
Supply Current vs. Input Switching Frequency



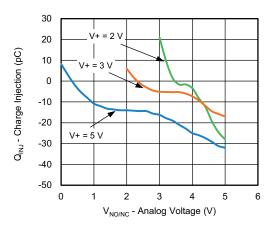
Switching Time vs. Temperature and Supply Voltage



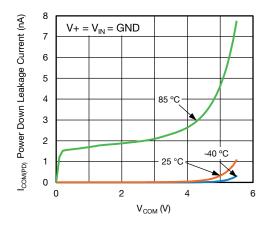
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



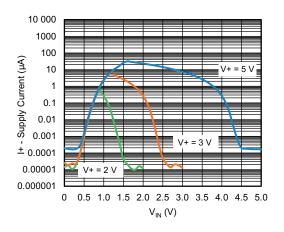
Switching Threshold vs. Supply Voltage



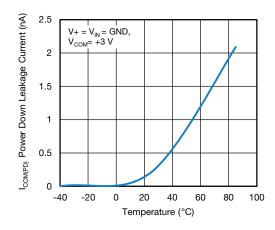
Charge Injection vs. Analog Voltage



Power Down Leakage Current vs. V_{COM}



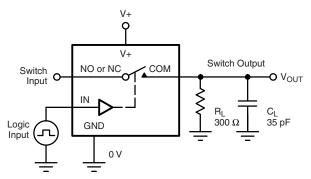
Supply Current vs. Enable Input Voltage



Power Down Leakage Current vs. Temperature

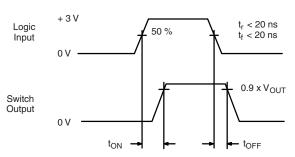


TEST CIRCUITS



C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time

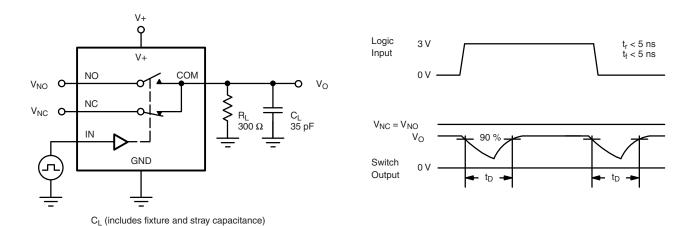


Fig. 2 - Break-Before-Make Interval

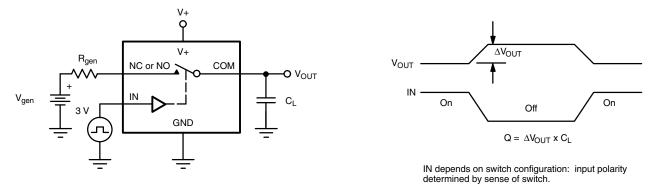


Fig. 3 - Charge Injection

TEST CIRCUITS

S18-0426-Rev. B, 23-Apr-18

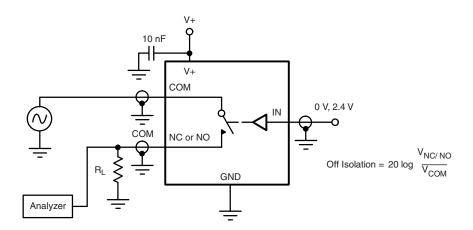


Fig. 4 - Off-Isolation

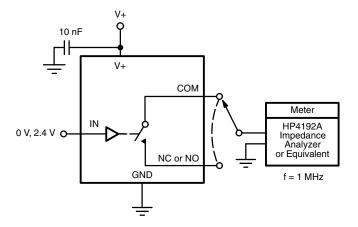


Fig. 5 - Channel Off/On Capacitance

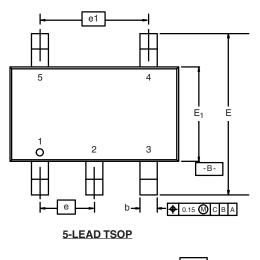
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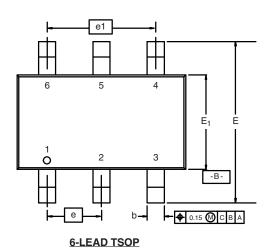




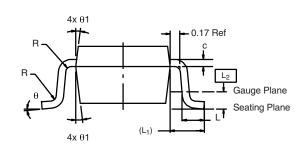
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C





-A-D · A_2 Seating Plane **a** 0.08 C -C- A₁

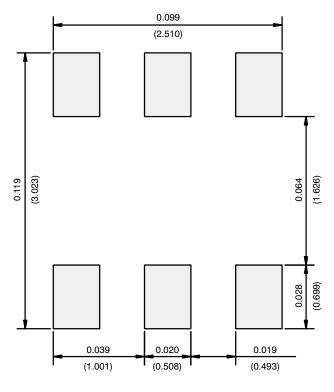


	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		(0.0374 BSC	;	
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁		0.60 Ref			0.024 Ref		
L ₂		0.25 BSC		0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1		7° Nom		7° Nom			
	ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

Document Number: 71200 www.vishay.com 18-Dec-06

VISHAY.

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)

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PI5A3166TAEX FSA634UCX TC4066BP(N,F) DG302BDJ-E3 PI5A100QEX HV2605FG-G HV2301FG-G RS2117YUTQK10
RS2118YUTQK10 RS2227XUTQK10 ADG452BRZ-REEL7 MAX4066ESD+ MAX391CPE+ MAX4730EXT+T MAX314CPE+
BU4066BCFV-E2 MAX313CPE+ BU4S66G2-TR NLAS3158MNR2G NLASB3157MTR2G TS3A4751PWR NLAS4157DFT2G
NLAS4599DFT2G NLAST4599DFT2G NLAST4599DTT1G DG300BDJ-E3 DG2503DB-T2-GE1 DG2502DB-T2-GE1
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FSA2275AUMX